











DLP660TE

DLPS163 - APRIL 2019

DLP660TE 0.66 4K UHD DMD

1 Features

- 0.66-Inch diagonal micromirror array
 - System displays 4K ultra high definition (UHD) 3840 x 2160 pixels on the screen
 - 5.4-Micron micromirror pitch
 - ±17° micromirror tilt (relative to flat surface)
 - Bottom illumination
- 2xLVDS input data bus
- Dedicated DLPC4422 display controller and DLPA100 power management IC and motor driver for reliable operation

2 Applications

- 4K UHD display
- Digital signage
- Laser TV
- Projection mapping

3 Description

The TI DLP660TE digital micromirror device (DMD) is a digitally controlled micro-opto-electromechanical system (MOEMS) spatial light modulator (SLM) that enables bright, affordable full 4K UHD display solutions. When coupled to an appropriate optical system, DLP660TE DMD displays true 4K UHD resolution (8.3M pixels on screen) and is capable of delivering accurate, detailed images to a variety of surfaces. The DLP660TE DMD, together with the DLPC4422 display controller and DLPA100 power and motor driver, comprise the DLP[®] 4K UHD chipset. This solution is a great fit for display systems that require high resolution, high brightness and system simplicity.

Device Information⁽¹⁾

PART NUMBER	PACKAGE	BODY SIZE (NOM)
DLP660TE	FYG (350)	35mm x 32mm

 For all available packages, see the orderable addendum at the end of the data sheet.

DLP® DLP660TE 0.66 4K UHD DMD

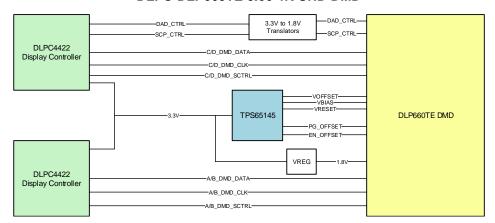




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4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

DATE	REVISION	NOTES
April 2019	*	Initial release.

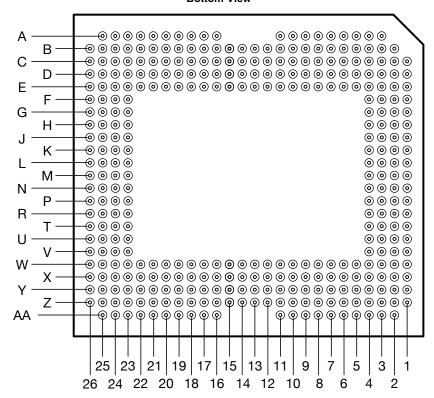
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5 Pin Configuration and Functions

Series 610 350-pin FYG Bottom View



CAUTION

To ensure reliable, long-term operation of the .66" UHD S610 DMD, it is critical to properly manage the layout and operation of the signals identified in the table below. For specific details and guidelines, refer to the *PCB Design Requirements for TI DLP Standard TRP Digital Micromirror Devices* application report before designing the board.



Pin Functions

P	PIN		runctions	DATA	D=000::===01		
NAME NO.		TYPE	TYPE SIGNAL RATE		DESCRIPTION		
DATA INPUTS			I				
D_AN(0)	C7						
D_AP(0)	C8						
D_AN(1)	D4						
D_AP(1)	E4						
D_AN(2)	C5						
D_AP(2)	C4						
D_AN(3)	D6						
D_AP(3)	C6						
D_AN(4)	D8						
D_AP(4)	D7						
D_AN(5)	D3						
D_AP(5)	E3						
D_AN(6)	В3						
D_AP(6)	C3						
D_AN(7)	E11						
D_AP(7)	E10	Input	2xLVDS		LVDS pair for Data Bus A (15:0)		
D_AN(8)	E6	iliput	ZXLVDS		EVDS pair for Data Bus A (13.0)		
D_AP(8)	E5						
D_AN(9)	B10						
D_AP(9)	C10						
D_AN(10)	B8						
D_AP(10)	B9						
D_AN(11)	C13						
D_AP(11)	C14						
D_AN(12)	D15						
D_AP(12)	E15						
D_AN(13)	B12						
D_AP(13)	B13						
D_AN(14)	B15						
D_AP(14)	B16						
D_AN(15)	C16						
D_AP(15)	C17						



Pin Functions (continued)

PI	IN			DATA	
NAME	NO.	TYPE	SIGNAL	RATE	DESCRIPTION
D_BN(0)	Y8				
D_BP(0)	Y7				
D_BN(1)	X4				
D_BP(1)	W4				
D_BN(2)	Z3				
D_BP(2)	Y3				
D_BN(3)	X6				
D_BP(3)	Y6				
D_BN(4)	X8				
D_BP(4)	X7				
D_BN(5)	Х3				
D_BP(5)	W3				
D_BN(6)	W15				
D_BP(6)	X15				
D_BN(7)	W11				
D_BP(7)	W10	loout	2xLVDS		LVDS pair for Data Bus B (15:0)
D_BN(8)	W6	Input	ZXLVDS		LVD3 pail for Data Bus B (13.0)
D_BP(8)	W5				
D_BN(9)	AA9				
D_BP(9)	AA10				
D_BN(10)	Z8				
D_BP(10)	Z 9				
D_BN(11)	Y13				
D_BP(11)	Y14				
D_BN(12)	Z10				
D_BP(12)	Y10				
D_BN(13)	Z12				
D_BP(13)	Z13				
D_BN(14)	Z15				
D_BP(14)	Z16				
D_BN(15)	Y16				
D_BP(15)	Y17				



Pin Functions (continued)

PI	N		016	DATA	
NAME NO.		TYPE	SIGNAL	RATE	DESCRIPTION
D_CN(0)	C18				
D_CP(0)	C19				
D_CN(1)	A20				
D_CP(1)	A19				
D_CN(2)	L23				
D_CP(2)	K23				
D_CN(3)	C23				
D_CP(3)	B23				
D_CN(4)	G23				
D_CP(4)	H23				
D_CN(5)	H24				
D_CP(5)	G24				
D_CN(6)	B18				
D_CP(6)	B19				
D_CN(7)	C21				
D_CP(7)	B21	loout	2xLVDS	LVDS pair for Data Bus C (15:0)	
D_CN(8)	D23	Input	ZXLVDS		LVDS pair for Data Bus C (15.0)
D_CP(8)	E23				
D_CN(9)	D25				
D_CP(9)	C25				
D_CN(10)	L24				
D_CP(10)	K24				
D_CN(11)	K25				
D_CP(11)	J25				
D_CN(12)	B24				
D_CP(12)	A24				
D_CN(13)	D26				
D_CP(13)	C26				
D_CN(14)	G25				
D_CP(14)	F25				
D_CN(15)	K26				
D_CP(15)	J26				



Pin Functions (continued)

PI	N					
NAME	NO.	TYPE	SIGNAL	DATA RATE	DESCRIPTION	
D_DN(0)	Y18					
D_DP(0)	Y19	_				
D_DN(1)	AA20	7				
D_DP(1)	AA19	7				
D_DN(2)	N23	7				
D_DP(2)	P23	7				
D_DN(3)	Y23	7				
D_DP(3)	Z23	1				
D_DN(4)	U23	1				
D_DP(4)	T23	1				
D_DN(5)	T24	7				
D_DP(5)	U24	7				
D_DN(6)	Z18	7				
D_DP(6)	Z19					
D_DN(7)	Y21	7				
D_DP(7)	Z21	1	0.11/100		11/20 : (2 . 2 . 2 . 2 . 2 . 2 . 2 . 2 . 2	
D_DN(8)	X23	Input	2xLVDS		LVDS pair for Data Bus D (15:0)	
D_DP(8)	W23					
D_DN(9)	X25					
D_DP(9) D_DN(10) D_DP(10)	Y25					
	N24					
	P24					
D_DN(11)	P25					
D_DP(11)	R25					
D_DN(12)	Z24					
D_DP(12)	AA24					
D_DN(13)	X26					
D_DP(13)	Y26					
D_DN(14)	U25					
D_DP(14)	V25					
D_DN(15)	P26					
D_DP(15)	R26					
DCLK_AN	B6	Input			LVDS pair for Data Clock A	
DCLK_AP	B5	прис			Evolo pair for bata clock A	
DCLK_BN	Z6	Input			LVDS pair for Data Clock B	
DCLK_BP	Z5	прис			2.50 pair for bata clock b	
DCLK_CN	G26	Input			LVDS pair for Data Clock C	
DCLK_CP	F26	прис			2.20 pair 101 Bata 0100k 0	
DCLK_DN	U26	Input			LVDS pair for Data Clock D.	
DCLK_DP	V26	прас			2.20 pair 101 Bata 0100k B.	
DATA CONTROL INPU	T.				Т.	
SCTRL_AN	A10	Input			LVDS pair for Serial Control (Sync) A	
SCTRL_AP	A9	pat			Cyno, re	
SCTRL_BN	Y4	Input			LVDS pair for Serial Control (Sync) B	
SCTRL_BP	Y5	mput			2.20 pair for Sorial Control (Oyrio) D	



Pin Functions (continued)

PIN	PIN							
NAME	NO.	TYPE	SIGNAL	DATA RATE	THE COUDING			
SCTRL_CN	E24							
SCTRL_CP	D24	Input			LVDS pair for Serial Control (Sync) C			
SCTRL DN	W24							
SCTRL_DP	X24	Input			LVDS pair for Serial Control (Sync) D			
DAD CONTROL INPUTS					1			
RESET_ADDR(0)	R3							
RESET_ADDR(1)	R4				Reset Driver Address Select. Bond Pad			
RESET_ADDR(2)	T3	Input			connects to an internal Pull Down circuit			
RESET_ADDR(3)	U2							
RESET_MODE(0)	P4				Reset Driver Mode Select, Bond Pad			
RESET_MODE(1)	V3	Input			connects to an internal Pull Down circuit			
RESET_OEZ	R2	Input			Active Low. Output Enable signal for internal Reset Driver circuitry. Bond Pad connects to an internal Pull Up circuit			
RESET_SEL(0)	P3	loout			Reset Driver Level Select. Bond Pad			
RESET_SEL(1)	V2	Input			connects to an internal Pull Down circuit			
RESET_STROBE	W8	Input			Rising edge on RESET_STROBE latches in the control signals. Bond Pad connects to an internal Pull Down circuit			
RESETZ	U4	Input			Active Low. Places reset circuitry in known VOFFSET state. Bond Pad connects to an internal Pull Down circuit			
SCP CONTROL	I	1			-1			
SCPCLK	W17	Input			Serial Communications Port Clock. SCPCLK is only active when SCPENZ goes low. Bond Pad connects to an internal Pull Down circuit			
SCPDI	W18	Input			Serial Communications Port Data. Synchronous to the Rising Edge of SCPCLK. Bond Pad connects to an internal Pull Down circuit			
SCPENZ	X18	Input			Active Low Serial Communications Port Enable. Bond Pad connects to an internal Pull Down circuit			
SCPDO	W16	Output			Serial Communications Port output			
EXTERNAL REGULATO	R SIGNALS							
EN_BIAS	J4	Output			Active High. Enable signal for external VBIAS regulator			
EN_OFFSET	Н3	Output			Active High. Enable signal for external VOFFSET regulator			
EN_RESET	J3	Output			Active High. Enable signal for external VRESET regulator			
OTHER SIGNALS								
RESET_IRQZ	U3	Output			Active Low. Output Interrupt to DLP controller (ASIC)			
TEMP_PLUS	E16	Analog			Temperature Sensor Diode Anode. (1)			
TEMP_MINUS	E17	Analog			Temperature Sensor Diode Cathode. (1)			
POWER								
VBIAS	A5, A6, A7	Power			Power supply for Positive Bias level of micromirror reset signal			

(1) VSS must be connected for proper DMD operation.



Pin Functions (continued)

PI	N	1 III I dilotte		•			
NAME NO.		TYPE	SIGNAL	DATA RATE	DESCRIPTION		
V _{cc}	A8, B2, C1, D1, D10, D12, D19, E1, E19, E20, E21, F1, K1, L1, M1, N1, P1,V1, W1, W19, W20, W21, X1, X10, X12, X19, Y1, Z1, Z2, AA2, AA8,	Power			Power supply for low voltage CMOS logic. Power supply for normal high voltage at micromirror address electrodes. Power supply for Offset level of Dow during power down sequence		
V _{CCI}	A11, A16, A17, A18, A21, A22, A23, AA11, AA16, AA17, AA18, AA21, AA22, AA23,	Power			Power supply for low voltage CMOS LVDS interface		
V _{OFFSET}	A3, A4, A25, B26, L26, M26, N26, Z26, AA3, AA4, AA25	Power			Power supply for high voltage CMOS logic. Power supply for stepped high voltage at micromirror address electrodes. Power supply for Offset level of MBRST(15:0)		
V _{RESET}	G1, H1, J1, R1, T1, U1	Power			Power supply for Negative Reset level of micromirror reset signal		
V _{SS} (Ground)	B4, B7, B11, B14, B17, B20, B22, B25, C2, C9, C20, C22, C24, D2, D5, D9, D11, D14, D18, D20, D21, D22, E2, E26, F4, F23, F24, H2, H4, H25, H26, J23, J24, K2, L2, L3, L4, L25, M2, M3, M4, M23, M24, M25, N2, N3, N25, P2,R23, R24, T2, T4, T25, T26, V4, V23, V24, W2, W7, W9, W22, W25, W26, X2, X5, X9, X11, X20, X21, X22, Y24, Z4, Z7, Z11, Z14, Z17, Z20, Z22, Z25	Ground			Common Return for all power		
RESERVED SIGNALS							
RESERVED_PFE	E18	Ground			Connect to ground on the DLP® system board. Bond Pad connects to an internal Pull Down circuit		
RESERVED_TM	G4	Ground			Connect to ground on the DLP® system board. Bond Pad connects to an internal Pull Down circuit		
RESERVED_TP0	E8	Input			Do Not Connect on the DLP® system board		
RESERVED_TP1	J2	Input			Do Not Connect on the DLP® system board		
RESERVED_TP2	G2	Input		_	Do Not Connect on the DLP® system board		
RESERVED_BA	N4	Output			Do Not Connect on the DLP® system board		
RESERVED_BB	K4	Output		_	Do Not Connect on the DLP® system board		
RESERVED_BC	X17	Output			Do Not Connect on the DLP® system board		
RESERVED_BD	D17	Output			Do Not Connect on the DLP® system board		





Pin Functions - Test Pads

Tim functions Test Fude					
Pin Number	System Board				
E13	Do not connect				
C12	Do not connect				
D13	Do not connect				
C11	Do not connect				
E14	Do not connect				
E12	Do not connect				
C15	Do not connect				
D16	Do not connect				
W13	Do not connect				
Y12	Do not connect				
X13	Do not connect				
Y11	Do not connect				
W14	Do not connect				
W12	Do not connect				
Y15	Do not connect				
X16	Do not connect				

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Specifications

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6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)

		MIN	MAX	UNIT
Supply Voltages	,		,	
V _{CC}	Supply voltage for LVCMOS core logic ⁽¹⁾	- 0.5	2.3	V
V _{CCI}	Supply voltage for LVDS receivers (1)	- 0.5	2.3	V
V _{OFFSET}	Supply voltage for HVCMOS and micromirror electrode (1)(2)	- 0.5	11	V
V _{BIAS}	Supply voltage for micromirror electrode ⁽¹⁾	- 0.5	19	V
V _{RESET}	Supply voltage for micromirror electrode ⁽¹⁾	– 15	-0.3	V
V _{CC} - V _{CCI}	Supply voltage delta (absolute value) (3)		0.3	V
V _{BIAS} – V _{OFFSET}	Supply voltage delta (absolute value) (4)		11	V
V _{BIAS} – V _{RESET}	Supply voltage delta (absolute value) ⁽⁵⁾		34	V
Input Voltages	,		,	
	Input voltage for all other LVCMOS input pins (1)	- 0.5	V _{CC} + 0.5	V
	Input voltage for all other LVDS input pins ⁽¹⁾⁽⁵⁾	- 0.5	V _{CCI} + 0.5	V
V _{ID}	Input differential voltage (absolute value) (5)		500	mV
I _{ID}	Input differential current ⁽⁶⁾		6.25	mA
Clocks	,		,	
f_{CLOCK}	Clock frequency for LVDS interface, DCLK_A		400	MHz
fclock	Clock frequency for LVDS interface, DCLK_B		400	MHz
f _{CLOCK}	Clock frequency for LVDS interface, DCLK_C		400	MHz
fCLOCK	Clock frequency for LVDS interface, DCLK_D		400	MHz
Environmental				
T _{ARRAY} and T _{WINDOW}		0	90	°C
Temperature, non–operating ⁽⁷⁾	Temperature, operating ⁽⁷⁾	- 40	90	°C
T _{DELTA}	Absolute Temperature delta between any point on the window edge and the ceramic test point TP1 ⁽⁸⁾		30	°C
T _{DP}	Dew Point Temperature, operating and non–operating (noncondensing)		81	°C

- (1) All voltages are referenced to common ground V_{SS}. V_{BIAS}, V_{CC}, V_{CCI}, V_{OFFSET}, and V_{RESET} power supplies are all required for proper DMD operation. V_{SS} must also be connected.
- V_{OFFSET} supply transients must fall within specified voltages.
- (3) Exceeding the recommended allowable voltage difference between V_{CC} and V_{CCI} may result in excessive current draw.
 (4) Exceeding the recommended allowable voltage difference between V_{BIAS} and V_{OFFSET} may result in excessive current draw.
- Exceeding the recommended allowable voltage difference between V_{BIAS} and V_{RESET} may result in excessive current draw.
- LVDS differential inputs must not exceed the specified limit or damage may result to the internal termination resistors.
- The highest temperature of the active array (as calculated using Micromirror Array Temperature Calculation) or of any point along the window edge as defined in Figure 11. The locations of thermal test points TP2, TP3, TP4 and TP5 in Figure 11 are intended to measure the highest window edge temperature. If a particular application causes another point on the window edge to be at a higher temperature, that point should be used.
- Temperature delta is the highest difference between the ceramic test point 1 (TP1) and anywhere on the window edge as shown in Figure 11. The window test points TP2, TP3, TP4 and TP5 shown in Figure 11 are intended to result in the worst case delta. If a particular application causes another point on the window edge to result in a larger delta temperature, that point should be used.

6.2 Storage Conditions

Applicable for the DMD as a component or non-operating in a system

		MIN	MAX	UNIT
T _{stg}	DMD storage temperature	- 40	80	°C
T _{DP-AVG}	Average dew point temperature, (non-condensing) (1)		28	°C
$T_{DP\text{-MAX}}$	Elevated dew point temperature range , (non-condensing) (2)	28	36	°C
CT _{ELR}	Cumulative time in elevated dew point temperature range		24	Months

The average over time (including storage and operating) that the device is not in the elevated dew point temperature range.

Exposure to dew point temperatures in the elevated range during storage and operation should be limited to less than a total cumulative time of CT_{ELR}.

6.3 ESD Ratings

			VALUE	UNIT
V _(ESD) Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±2000	\/	
	Charged device model (CDM), per JEDEC specification JESD22-C101 (2)	±500	V	

- JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.4 Recommended Operating Conditions

Over operating free-air temperature range (unless otherwise noted). The functional performance of the device specified in this data sheet is achieved when operating the device within the limits defined by the Recommended Operating Conditions. No level of performance is implied when operating the device above or below the Recommended Operating Conditions limits.

		MIN	NOM	MAX	UNIT
Voltage Supply		'		•	
V _{CC}	LVCMOS logic supply voltage ⁽¹⁾	1.65	1.8	1.95	V
V _{CCI}	LVCMOS LVDS Interface supply voltage ⁽¹⁾	1.65	1.8	1.95	V
V _{OFFSET}	Mirror electrode and HVCMOS voltage ⁽¹⁾⁽²⁾	9.5	10	10.5	V
V _{BIAS}	Mirror electrode voltage ⁽¹⁾	17.5	18	18.5	V
V _{RESET}	Mirror electrode voltage ⁽¹⁾	- 14.5	- 14	- 13.5	V
V _{CC} - V _{CCI}	Supply voltage delta (absolute value) ⁽³⁾		0	0.3	V
V _{BIAS} - V _{OFFSET}	Supply voltage delta (absolute value) ⁽⁴⁾			10.5	V
V _{BIAS} - V _{RESET}	Supply voltage delta (absolute value) ⁽⁵⁾			33	V
LVCMOS Interfac	e	•		*	
V _{IH(DC)}	DC input high voltage ⁽⁶⁾	0.7 × V _{CC}		V _{CC} + 0.3	V
V _{IL(DC)}	DC input low voltage ⁽⁶⁾	- 0.3		0.3 × V _{CC}	V
V _{IH(AC)}	AC input high voltage ⁽⁶⁾	0.8 × V _{CC}		V _{CC} + 0.3	V
V _{IL(AC)}	AC input low voltage ⁽⁶⁾	- 0.3		0.2 × V _{CC}	V
t _{PWRDNZ}	PWRDNZ pulse width ⁽⁷⁾	10			ns
SCP Interface					
$f_{\sf SCPCLK}$	SCP clock frequency ⁽⁸⁾			500	kHz
t _{SCP_PD}	Propagation delay, Clock to Q, from rising–edge of SCPCLK to valid SCPDO ⁽⁹⁾	0		900	ns
t _{SCP_NEG_ENZ}	Time between falling-edge of SCPENZ and the first rising- edge of SCPCLK	2			μs

- (1) All voltages are referenced to common ground VSS. VBIAS, VCC, VCCI, VOFFSET, and VRESET power supplies are all required for proper DMD operation. VSS must also be connected.
- VOFFSET supply transients must fall within specified max voltages.
- To prevent excess current, the supply voltage delta |VCCI VCC| must be less than specified limit. See Power Supply Recommendations, Figure 15, and Table 8.
- (4) To prevent excess current, the supply voltage delta |VBIAS VOFFSET| must be less than specified limit. See Power Supply Recommendations, Figure 15, and Table 8.
- (5) To prevent excess current, the supply voltage delta |VBIAS VRESET| must be less than specified limit. See Power Supply Recommendations, Figure 15, and Table 8.
- (6) Low-speed interface is LPSDR and adheres to the Electrical Characteristics and AC/DC Operating Conditions table in JEDEC Standard No. 209B, "Low-Power Double Data Rate (LPDDR)" JESD209B.Tester Conditions for VIH and VIL. (a) Frequency = 60 MHz. Maximum Rise Time = 2.5 ns @ (20% - 80%)
 - (b) Frequency = 60 MHz. Maximum Fall Time = 2.5 ns @ (80% 20%)
- PWRDNZ input pin resets the SCP and disables the LVDS receivers. PWRDNZ input pin overrides SCPENZ input pin and tristates the SCPDO output pin.

Product Folder Links: DLP660TE

- The SCP clock is a gated clock. Duty cycle must be 50% ± 10%. SCP parameter is related to the frequency of DCLK.
- (9)See Figure 2.

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ISTRUMENTS



Recommended Operating Conditions (continued)

Over operating free-air temperature range (unless otherwise noted). The functional performance of the device specified in this data sheet is achieved when operating the device within the limits defined by the *Recommended Operating Conditions*. No level of performance is implied when operating the device above or below the *Recommended Operating Conditions* limits.

•				•	
		MIN	NOM	MAX	UNIT
t _{SCP_POS_ENZ}	Time between falling-edge of SCPCLK and the rising- edge of SCPENZ	2			μs
t _{SCP_DS}	SCPDI Clock Setup time (before SCPCLK falling edge) ⁽⁹⁾	800			ns
t _{SCP_DH}	SCPDI Hold time (after SCPCLK falling edge) (9)	900			ns
t _{SCP_PW_ENZ}	SCPENZ inactive pulse width (high level)	2			μs
LVDS Interface					
$f_{ extsf{CLOCK}}$	Clock frequency for LVDS interface (all channels), DCLK ⁽¹⁰⁾			400	MHz
V _{ID}	Input differential voltage (absolute value) ⁽¹¹⁾	150	300	440	mV
V _{CM}	Common mode voltage ⁽¹¹⁾	1100	1200	1300	mV
V _{LVDS}	LVDS voltage ⁽¹¹⁾	880		1520	mV
t _{LVDS_RSTZ}	Time required for LVDS receivers to recover from PWRDNZ			2000	ns
Z _{IN}	Internal differential termination resistance	80	100	120	Ω
Z _{LINE}	Line differential impedance (PWB/trace)	90	100	110	Ω
Environmental				1	
-	Array temperature, Long-term operational ⁽¹²⁾⁽¹³⁾⁽¹⁴⁾⁽¹⁵⁾	10		40 to 70 ⁽¹⁴⁾	°C
T _{ARRAY}	Array temperature, Short–term operational ⁽¹³⁾⁽¹⁶⁾	0		10	°C
T _{WINDOW}	Window temperature – operational			85	°C
T _{DELTA}	Absolute Temperature delta between any point on the window edge and the ceramic test point TP1(17)(18)			14	°C
T _{DP} -AVG	Average dew point average temperature (non–condensing) ⁽¹⁹⁾			28	°C
T _{DP-MAX}	Elevated dew point temperature range (non-condensing) ⁽²⁰⁾	28		36	°C
CT _{ELR}	Cumulative time in elevated dew point temperature range			24	Months
L	Operating system luminance ⁽¹⁸⁾			7000	lm
ILL _{UV}	Illumination Wavelengths < 395 nm ⁽¹²⁾⁽²¹⁾		0.68	2.00	mW/cm ²
ILL _{VIS}	Illumination Wavelengths between 395 nm and 800 nm ⁽²¹⁾		Thermally limited		mW/cm ²
ILL _{IR}	Illumination Wavelengths > 800 nm ⁽²¹⁾			10	mW/cm ²

- (10) See LVDS Timing Requirements in *Timing Requirements* and Figure 6.
- (11) See Figure 5 LVDS Waveform Requirements.
- (12) Simultaneous exposure of the DMD to the maximum Recommended Operating Conditions for temperature and UV illumination will reduce device lifetime.
- (13) The array temperature cannot be measured directly and must be computed analytically from the temperature measured at test point 1 (TP1) shown in Figure 11 and the package thermal resistance *Micromirror Array Temperature Calculation*.
- (14) Per Figure 1, the maximum operational array temperature should be derated based on the micromirror landed duty cycle that the DMD experiences in the end application. See *Micromirror Landed-On/Landed-Off Duty Cycle* for a definition of micromirror landed duty cycle.
- (15) Long-term is defined as the usable life of the device.
- (16) Array temperatures beyond those specified as long-term are recommended for short-term conditions only (power-up). Short-term is defined as cumulative time over the usable life of the device and is less than 500 hours.
- (17) Temperature delta is the highest difference between the ceramic test point 1 (TP1) and anywhere on the window edge as shown in Figure 11. The window test points TP2, TP3, TP4 and TP5 shown in Figure 11 are intended to result in the worst case delta temperature. If a particular application causes another point on the window edge to result in a larger delta temperature, that point should be used.
- (18) DMD is qualified at the combination of the maximum temperature and maximum lumens specified. Operation of the DMD outside of these limits has not been tested.
- (19) The average over time (including storage and operating) that the device is not in the elevated dew point temperature range.
- (20) Exposure to dew point temperatures in the elevated range during storage and operation should be limited to less than a total cumulative time of CT_{FLR}.
- (21) Supported for Video applications only



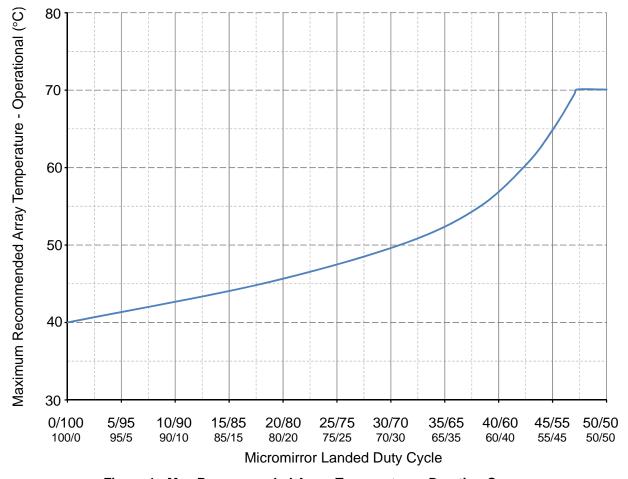


Figure 1. Max Recommended Array Temperature - Derating Curve



6.5 Thermal Information

	DLP660TE	
THERMAL METRIC	FYG Package	UNIT
	350 PINS	
Thermal resistance, active area to test point 1 (TP1) ⁽¹⁾	0.60	°C/W

(1) The DMD is designed to conduct absorbed and dissipated heat to the back of the package. The cooling system must be capable of maintaining the package within the temperature range specified in the *Recommended Operating Conditions*. The total heat load on the DMD is largely driven by the incident light absorbed by the active area; although other contributions include light energy absorbed by the window aperture and electrical power dissipation of the array. Optical systems should be designed to minimize the light energy falling outside the window clear aperture since any additional thermal load in this area can significantly degrade the reliability of the device.

6.6 Electrical Characteristics

Over operating free-air temperature range (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP MAX	UNIT
V_{OH}	High level output voltage	$V_{CC} = 1.8 \text{ V}, I_{OH} = -2 \text{ mA}$	0.8 x V _{CC}		V
V_{OL}	Low level output voltage	$V_{CC} = 1.95 \text{ V}, I_{OL} = 2 \text{ mA}$		0.2 x V _{CC}	V
l _{OZ}	High impedance output current	V _{CC} = 1.95 V	-40	25	μΑ
I _{IL}	Low level input current	V _{CC} = 1.95 V, VI = 0	-1		μΑ
I _{IH}	High level input current (1)	V _{CC} = 1.95 V, VI = V _{CC}		110	μΑ
I _{CC}	Supply current VCC	V _{CC} = 1.95 V		1200	mA
I _{CCI}	Supply current VCCI	V _{CCI} = 1.95 V		330	mA
I _{OFFSET}	Supply current VOFFSET (2)	V _{OFFSET} = 10.5 V		13.2	mA
I _{BIAS}	Supply current VBIAS (2) (3)	V _{BIAS} = 18.5 V		-3.641	mA
I _{RESET}	Supply current VRESET (3)	V _{RESET} = - 14.5 V		9.02	mA
	Supply power dissipation Total			3320.25	mW

- (1) Applies to LVCMOS pins only. Excludes LVDS pins and test pad pins.
- (2) To prevent excess current, the supply voltage delta |VBIAS VOFFSET| must be less than the specified limit in Recommended Operating Conditions.
- (3) To prevent excess current, the supply voltage delta |VBIAS VRESET| must be less than specified limit in Recommended Operating Conditions.

6.7 Capacitance at Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

	PARAMETER		MIN	TYP	MAX	UNIT
C _{I_lvds}	LVDS Input Capacitance 2xLVDS	f = 1 MHz			20	pF
C _{I_nonlvds}	Non-LVDS Input capacitance 2xLVDS	f = 1 MHz			20	pF
C _{I_tdiode}	Temp Diode Input capacitance 2xLVDS	f= 1 MHz			30	pF
C _O	Output Capacitance	f = 1 MHz			20	pF



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6.8 Timing Requirements

	<u> </u>		MIN	NOM	MAX	UNIT
SCP ⁽¹⁾					'	
t _r	Rise slew rate	20% to 80% reference points	1		3	V/ns
t _f	Fall slew rate	80% to 20% reference points	1		3	V/ns
LVDS ⁽²⁾						
t _r	Rise slew rate	20% to 80% reference points	0.7	1		V/ns
t _f	Fall slew rate	80% to 20% reference points	0.7	1		V/ns
t _C	Clock Cycle	DCLK_A, LVDS pair	2.5			ns
t _C	Clock Cycle	DCLK_B, LVDS pair	2.5			ns
t _C	Clock Cycle	DCLK_C,LVDS pair	2.5			ns
t _C	Clock Cycle	DCLK_D, LVDS pair	2.5			ns
t _W	Pulse Width	DCLK_A LVDS pair	1.19	1.25		ns
t _W	Pulse Width	DCLK_B LVDS pair	1.19	1.25		ns
t _W	Pulse Width	DCLK_C LVDS pair	1.19	1.25		ns
t _W	Pulse Width	DCLK_D LVDS pair	1.19	1.25		ns
t _{Su}	Setup Time	D_A(15:0) before DCLK_A, LVDS pair	0.325			ns
t _{Su}	Setup Time	D_B(15:0) before DCLK_B, LVDS pair	0.325			ns
t _{Su}	Setup Time	D_C(15:0) before DCLK_C, LVDS pair	0.325			ns
t _{Su}	Setup Time	D_D(15:0) before DCLK_D, LVDS pair	0.325			ns
t _{Su}	Setup Time	SCTRL_A before DCLK_A, LVDS pair	0.325			ns
t _{Su}	Setup Time	SCTRL_B before DCLK_B, LVDS pair	0.325			ns
t _{Su}	Setup Time	SCTRL_C before DCLK_C, LVDS pair	0.325			ns
t _{Su}	Setup Time	SCTRL_D before DCLK_D, LVDS pair	0.325			ns
t _h	Hold Time	D_A(15:0) after DCLK_A, LVDS pair	0.145			ns
t _h	Hold Time	D_B(15:0) after DCLK_B, LVDS pair	0.145			ns
t _h	Hold Time	D_C(15:0) after DCLK_C, LVDS pair	0.145			ns
t _h	Hold Time	D_D(15:0) after DCLK_D, LVDS pair	0.145			ns
t _h	Hold Time	SCTRL_A after DCLK_A, LVDS pair	0.145			ns
t _h	Hold Time	SCTRL_B after DCLK_B, LVDS pair	0.145			ns
t _h	Hold Time	SCTRL_C after DCLK_C, LVDS pair	0.145			ns
t _h	Hold Time	SCTRL_D after DCLK_D, LVDS pair	0.145			ns
LVDS ⁽²⁾						
t _{SKEW}	Skew Time	Channel B relative to Channel A ⁽³⁾⁽⁴⁾ , LVDS pair	-1.25		+1.25	ns
t _{SKEW}	Skew Time	Channel D relative to Channel C ⁽⁵⁾⁽⁶⁾ , LVDS pair	-1.25		+1.25	ns

- (1) See Figure 3 for Rise Time and Fall Time for SCP.
- (2) See Figure 5 for Timing Requirements for LVDS.
- (3) Channel A (Bus A) includes the following LVDS pairs: DCLK_AN and DCLK_AP, SCTRL_AN and SCTRL_AP, D_AN(15:0) and D_AP(15:0).
- (4) Channel B (Bus B) includes the following LVDS pairs: DCLK_BN and DCLK_BP, SCTRL_BN and SCTRL_BP, D_BN(15:0) and D_BP(15:0).
- (5) Channel C (Bus C) includes the following LVDS pairs: DCLK_CN and DCLK_CP, SCTRL_CN and SCTRL_CP, D_CN(15:0) and D_CP(15:0).
- (6) Channel D (Bus D) includes the following LVDS pairs: DCLK_DN and DCLK_DP, SCTRL_DN and SCTRL_DP, D_DN(15:0) and D_DP(15:0).

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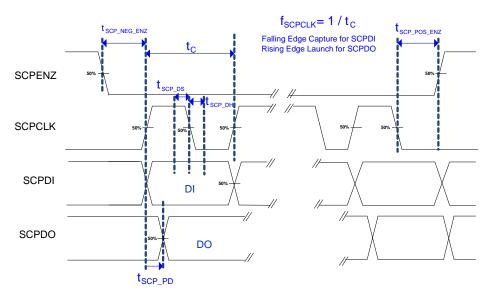


Figure 2. SCP Timing Requirements

See Recommended Operating Conditions for $f_{\text{SCPCLK}}, \, t_{\text{SCP_DB}}, \, t_{\text{SCP_DH}}$ and $t_{\text{SCP_PD}}$ specifications.

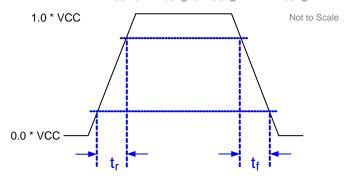


Figure 3. SCP Requirements for Rise and Fall

See *Timing Requirements* for t_r and t_f specifications and conditions.

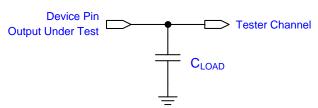


Figure 4. Test Load Circuit for Output Propagation Measurement

For output timing analysis, the tester pin electronics and its transmission line effects must be taken into account. System designers should use IBIS or other simulation tools to correlate the timing reference load to a system environment.

Not to Scale

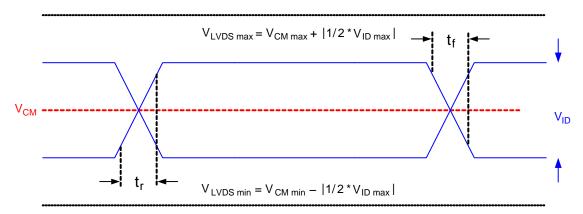


Figure 5. LVDS Waveform Requirements

See Recommended Operating Conditions for V_{CM} , V_{ID} , and V_{LVDS} specifications and conditions.

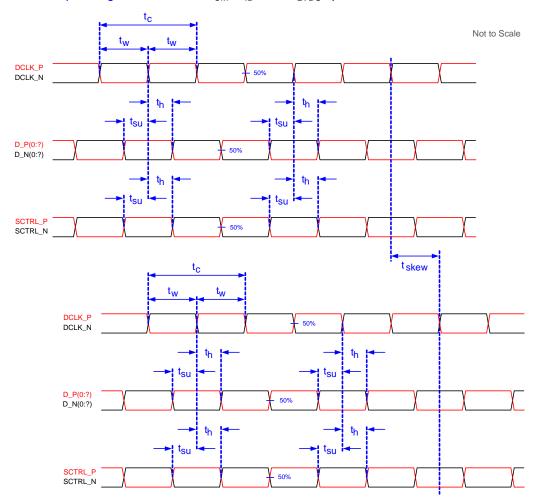


Figure 6. Timing Requirements

See *Timing Requirements* for timing requirements and LVDS pairs per channel (bus) defining $D_P(0:x)$ and $D_N(0:x)$.



6.9 System Mounting Interface Loads

Table 1. System Mounting Interface Loads

PARAMETER		MIN	NOM	MAX	UNIT
Thermal interface area	Condition 1: Maximum load of 22.6 kg evenly			11.3	kg
Electrical interface area	distributed within each area below: (1)			11.3	kg
Thermal interface area	Condition 2: Maximum load of 22.6 kg evenly			0	kg
Electrical interface area	distributed within each area below: (1)			22.6	kg

(1) See Figure 7.

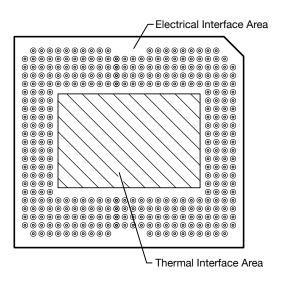


Figure 7. System Mounting Interface Loads

6.10 Micromirror Array Physical Characteristics

Table 2. Micromirror Array Physical Characteristics

PARAMETER DESCRIPTI	PARAMETER DESCRIPTION		
Number of active columns (1)	M	2716	micromirrors
Number of active rows (1)	N	1528	micromirrors
Micromirror (pixel) pitch (1)	Р	5.4	μm
Micromirror active array width (1)	Micromirror Pitch x number of active columns	14.67	mm
Micromirror active array height (1)	Micromirror Pitch x number of active rows	8.25	mm
Micromirror active border (Top / Bottom) (2)	Pond of micromirrors (POM)	56	micromirrors / side
Micromirror active border (Right / Left) (2)	Pond of micromirrors (POM)	20	micromirrors / side

⁽¹⁾ See Figure 8.

⁽²⁾ The structure and qualities of the border around the active array includes a band of partially functional micromirrors called the "Pond Of Mirrors" (POM). These micromirrors are structurally and/or electrically prevented from tilting toward the bright or "on" state but still require an electrical bias to tilt toward "off."



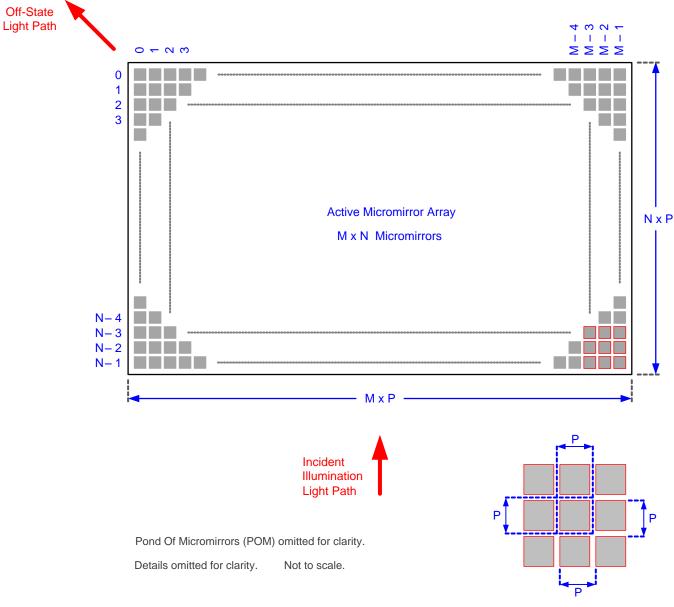


Figure 8. Micromirror Array Physical Characteristics

Refer to section *Micromirror Array Physical Characteristics* table for M, N, and P specifications.

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6.11 Micromirror Array Optical Characteristics

Table 3. Micromirror Array Optical Characteristics

PARAMETER		MIN	NOM	MAX	UNIT
Mirror Tilt angle, variation device to device (1) (2)		15.6	17.0	18.4	degrees
Number of out-of-specification	Adjacent micromirrors			0	
micromirrors (3)	Non-Adjacent micromirrors			10	micromirrors

- (1) Limits on variability of micromirror tilt angle are critical in the design of the accompanying optical system. Variations in tilt angle within a device may result in apparent non-uniformities, such as line pairing and image mottling, across the projected image. Variations in the average tilt angle between devices may result in colorimetric and system contrast variations.
- (2) See Figure 9.
- (3) An out-of-specification micromirror is defined as a micromirror that is unable to transition between the two landed states within the specified Micromirror Switching Time.

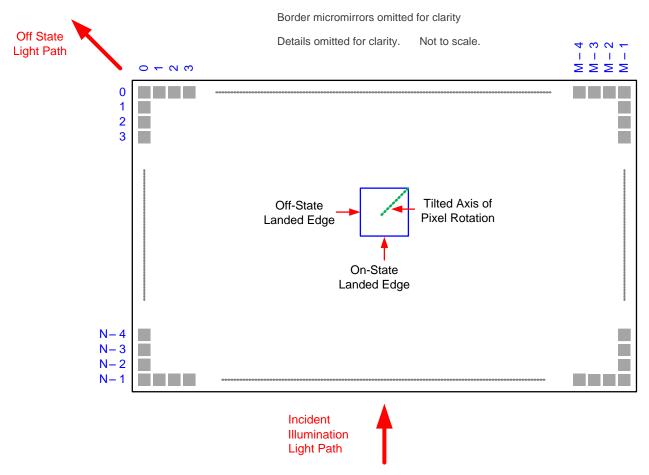


Figure 9. Micromirror Landed Orientation and Tilt

Refer to section Micromirror Array Physical Characteristics table for M, N, and P specifications.





6.12 Window Characteristics

Table 4. DMD Window Characteristics

PARAMETER	MIN	NOM	MAX	UNIT
Window Material Designation S610		Corning Eagle XG		
Window Refractive Index at 546.1 nm		1.5119		
Window Transmittance, minimum within the wavelength range 420–680 nm. Applies to all angles 0–30° AOI. $^{(1)}$ $^{(2)}$	97%			
Window Transmittance, average over the wavelength range 420–680 nm. Applies to all angles 30–45° AOI. (1) (2)	97%			

⁽¹⁾ Single-pass through both surfaces and glass.

6.13 Chipset Component Usage Specification

Reliable function and operation of the DLP660TE DMD requires that it be used in conjunction with the other components of the applicable DLP chipset, including those components that contain or implement TI DMD control technology. TI DMD control technology is the TI technology and devices for operating or controlling a DLP DMD.

⁽²⁾ AOI – angle of incidence is the angle between an incident ray and the normal to a reflecting or refracting surface.



7 Detailed Description

7.1 Overview

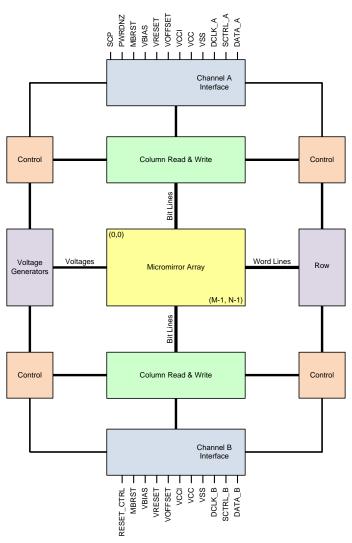
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The DMD is a 0.66 inch diagonal spatial light modulator which consists of an array of highly reflective aluminum micromirrors. The DMD is an electrical input, optical output micro-electrical-mechanical system (MEMS). The electrical interface is Low Voltage Differential Signaling (LVDS). The DMD consists of a two-dimensional array of 1-bit CMOS memory cells. The array is organized in a grid of M memory cell columns by N memory cell rows. Refer to the *Functional Block Diagram*. The positive or negative deflection angle of the micromirrors can be individually controlled by changing the address voltage of underlying CMOS addressing circuitry and micromirror reset signals (MBRST).

The DLP660TE DMD is part of the chipset comprising of the DLP660TE DMD, the DLPC4422 display controller and the DLPA100 power and motor driver. To ensure reliable operation, the DLP660TE DMD must always be used with the DLPC4422 display controller and the DLPA100 power and motor driver.

7.2 Functional Block Diagram

Not to Scale. Details Omitted for Clarity. See Accompanying Notes in this Section.



For pin details on Channels A, B, C, and D, refer to *Pin Configurations and Functions* and LVDS Interface section of *Timing Requirements*.

Figure 10. Functional Block Diagram

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7.3 Feature Description

7.3.1 Power Interface

The DMD requires 5 DC voltages: DMD_P3P3V, DMD_P1P8V, VOFFSET, VRESET, and VBIAS. DMD_P3P3V is created by the DLPA100 power and motor driver and is used on the DMD board to create the other 4 DMD voltages, as well as powering various peripherals (TMP411, I2C, and TI level translators). DMD_P1P8V is created by the TI PMIC LP38513S and provides the VCC voltage required by the DMD. VOFFSET (10V), VRESET (-14V), and VBIAS(18V) are made by the TI PMIC TPS65145 and are supplied to the DMD to control the micromirrors.

7.3.2 Timing

The data sheet provides timing at the device pin. For output timing analysis, the tester pin electronics and its transmission line effects must be taken into account. Figure 4 shows an equivalent test load circuit for the output under test. Timing reference loads are not intended as a precise representation of any particular system environment or depiction of the actual load presented by a production test. System designers should use IBIS or other simulation tools to correlate the timing reference load to a system environment. The load capacitance value stated is only for characterization and measurement of AC timing signals. This load capacitance value does not indicate the maximum load the device is capable of driving.

7.4 Device Functional Modes

DMD functional modes are controlled by the DLPC4422 display controller. See the DLPC4422 display controller data sheet or contact a TI applications engineer.

7.5 Optical Interface and System Image Quality Considerations

7.5.1 Optical Interface and System Image Quality

TI assumes no responsibility for end-equipment optical performance. Achieving the desired end-equipment optical performance involves making trade-offs between numerous component and system design parameters. Optimizing system optical performance and image quality strongly relate to optical system design parameter trades. Although it is not possible to anticipate every conceivable application, projector image quality and optical performance is contingent on compliance to the optical system operating conditions described in the following sections.

7.5.1.1 Numerical Aperture and Stray Light Control

The angle defined by the numerical aperture of the illumination and projection optics at the DMD optical area should be the same. This angle should not exceed the nominal device micromirror tilt angle unless appropriate apertures are added in the illumination and/or projection pupils to block out flat-state and stray light from the projection lens. The micromirror tilt angle defines DMD capability to separate the "ON" optical path from any other light path, including undesirable flat-state specular reflections from the DMD window, DMD border structures, or other system surfaces near the DMD such as prism or lens surfaces. If the numerical aperture exceeds the micromirror tilt angle, or if the projection numerical aperture angle is more than two degrees larger than the illumination numerical aperture angle, objectionable artifacts in the display's border and/or active area could occur.

7.5.1.2 Pupil Match

TI's optical and image quality specifications assume that the exit pupil of the illumination optics is nominally centered within 2° of the entrance pupil of the projection optics. Misalignment of pupils can create objectionable artifacts in the display's border and/or active area, which may require additional system apertures to control, especially if the numerical aperture of the system exceeds the pixel tilt angle.



Optical Interface and System Image Quality Considerations (continued)

7.5.1.3 Illumination Overfill

The active area of the device is surrounded by an aperture on the inside DMD window surface that masks structures of the DMD chip assembly from normal view, and is sized to anticipate several optical operating conditions. Overfill light illuminating the window aperture can create artifacts from the edge of the window aperture opening and other surface anomalies that may be visible on the screen. The illumination optical system should be designed to limit light flux incident anywhere on the window aperture from exceeding approximately 10% of the average flux level in the active area. Depending on the particular system's optical architecture, overfill light may have to be further reduced below the suggested 10% level in order to be acceptable.

7.6 Micromirror Array Temperature Calculation

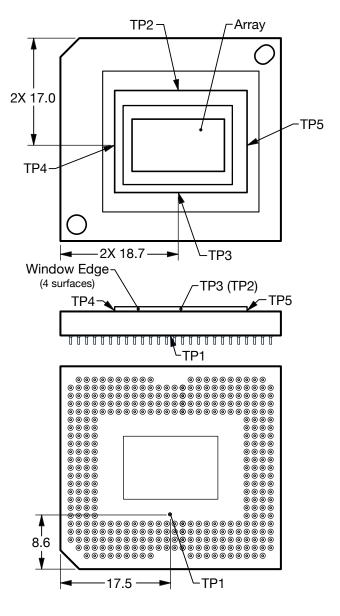


Figure 11. DMD Thermal Test Points

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Micromirror Array Temperature Calculation (continued)

Micromirror array temperature can be computed analytically from measurement points on the outside of the package, the package thermal resistance, the electrical power, and the illumination heat load. The relationship between micromirror array temperature and the reference ceramic temperature is provided by the following equations:

$$\begin{split} T_{ARRAY} &= T_{CERAMIC} + (Q_{ARRAY} \times R_{ARRAY-TO-CERAMIC}) \\ Q_{ARRAY} &= Q_{ELECTRICAL} + Q_{ILLUMINATION}) \end{split}$$

where

- T_{ARRAY} = computed array temperature (°C)
- T_{CERAMIC} = measured ceramic temperature (°C) (TP1 location)
- R_{ARRAY-TO-CERAMIC} = thermal resistance of package from array to ceramic TP1 (°C/Watt)
- Q_{ARRAY} = Total DMD power on the array (Watts) (electrical + absorbed)
- Q_{ELECTRICAL} = nominal electrical power
- $Q_{ILLUMINATION} = (C_{L2W} \times SL)$
- C_{L2W} = Conversion constant for screen lumens to power on DMD (Watts/Lumen)
- SL = measured screen lumens

The electrical power dissipation of the DMD is variable and depends on the voltages, data rates and operating frequencies. A nominal electrical power dissipation to use when calculating array temperature is 3.0 Watts. The absorbed power from the illumination source is variable and depends on the operating state of the micromirrors and the intensity of the light source. The equations shown above are valid for a 1-Chip DMD system with projection efficiency from the DMD to the screen of 87%.

The conversion constant CL2W is based on array characteristics. It assumes a spectral efficiency of 300 lumens/Watt for the projected light and illumination distribution of 83.7% on the active array, and 16.3% on the array border.

Sample calculations for typical projection application:

```
\begin{split} &Q_{ELECTRICAL} = 3.0 \text{ W} \\ &C_{L2W} = 0.00266 \\ &SL = 5000 \text{ Im} \\ &T_{CERAMIC} = 55.0^{\circ}\text{C} \\ &Q_{ARRAY} = 3.0 \text{ W} + (0.00266 \times 5000 \text{ Im}) = 16.3 \text{ W} \\ &T_{ARRAY} = 55.0^{\circ}\text{C} + (16.3 \text{ W} \times 0.60^{\circ}\text{C/W}) = 64.78^{\circ}\text{C} \end{split}
```

7.7 Micromirror Landed-On/Landed-Off Duty Cycle

7.7.1 Definition of Micromirror Landed-On/Landed-Off Duty Cycle

The micromirror landed-on/landed-off duty cycle (landed duty cycle) denotes the amount of time (as a percentage) that an individual micromirror is landed in the On state versus the amount of time the same micromirror is landed in the Off state.

As an example, a landed duty cycle of 100/0 indicates that the referenced pixel is in the On state 100% of the time (and in the Off state 0% of the time); whereas 0/100 would indicate that the pixel is in the Off state 100% of the time. Likewise, 50/50 indicates that the pixel is On 50% of the time and Off 50% of the time.

Note that when assessing landed duty cycle, the time spent switching from one state (ON or OFF) to the other state (OFF or ON) is considered negligible and is thus ignored.

Since a micromirror can only be landed in one state or the other (On or Off), the two numbers (percentages) always add to 100.

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Micromirror Landed-On/Landed-Off Duty Cycle (continued)

7.7.2 Landed Duty Cycle and Useful Life of the DMD

Knowing the long-term average landed duty cycle (of the end product or application) is important because subjecting all (or a portion) of the DMD's micromirror array (also called the active array) to an asymmetric landed duty cycle for a prolonged period of time can reduce the DMD's usable life.

Note that it is the symmetry/asymmetry of the landed duty cycle that is of relevance. The symmetry of the landed duty cycle is determined by how close the two numbers (percentages) are to being equal. For example, a landed duty cycle of 50/50 is perfectly symmetrical whereas a landed duty cycle of 100/0 or 0/100 is perfectly asymmetrical.

7.7.3 Landed Duty Cycle and Operational DMD Temperature

Operational DMD Temperature and Landed Duty Cycle interact to affect the DMD's usable life, and this interaction can be exploited to reduce the impact that an asymmetrical Landed Duty Cycle has on the DMD's usable life. This is quantified in the de-rating curve shown in Figure 1. The importance of this curve is that:

- All points along this curve represent the same usable life.
- All points above this curve represent lower usable life (and the further away from the curve, the lower the usable life).
- All points below this curve represent higher usable life (and the further away from the curve, the higher the usable life).

In practice, this curve specifies the Maximum Operating DMD Temperature that the DMD should be operated at for a give long-term average Landed Duty Cycle.

7.7.4 Estimating the Long-Term Average Landed Duty Cycle of a Product or Application

During a given period of time, the Landed Duty Cycle of a given pixel follows from the image content being displayed by that pixel.

For example, in the simplest case, when displaying pure-white on a given pixel for a given time period, that pixel will experience a 100/0 Landed Duty Cycle during that time period. Likewise, when displaying pure-black, the pixel will experience a 0/100 Landed Duty Cycle.

Between the two extremes (ignoring for the moment color and any image processing that may be applied to an incoming image), the Landed Duty Cycle tracks one-to-one with the gray scale value, as shown in Table 5.

Table 5. Gravscale Value and Landed Duty Cycle

Grayscale Value	Landed Duty Cycle
0%	0/100
10%	10/90
20%	20/80
30%	30/70
40%	40/60
50%	50/50
60%	60/40
70%	70/30
80%	80/20
90%	90/10
100%	100/0



Accounting for color rendition (but still ignoring image processing) requires knowing both the color intensity (from 0% to 100%) for each constituent primary color (red, green, and/or blue) for the given pixel as well as the color cycle time for each primary color, where "color cycle time" is the total percentage of the frame time that a given primary must be displayed in order to achieve the desired white point.

During a given period of time, the landed duty cycle of a given pixel can be calculated as follows:

Landed Duty Cycle = (Red_Cycle_% × Red_Scale_Value) + (Green_Cycle_% × Green_Scale_Value) + (Blue_Cycle_% × Blue_Scale_Value)

Where

 Red_Cycle_%, Green_Cycle_%, and Blue_Cycle_%, represent the percentage of the frame time that Red, Green, and Blue are displayed (respectively) to achieve the desired white point. (1)

For example, assume that the red, green and blue color cycle times are 50%, 20%, and 30% respectively (in order to achieve the desired white point), then the Landed Duty Cycle for various combinations of red, green, blue color intensities would be as shown in Table 6 and Table 7.

Table 6. Example Landed Duty Cycle for Full-Color, Color Percentage

Red Cycle Percentage	Green Cycle Percentage	Blue Cycle Percentage		
50%	20%	30%		

Table 7. Example Landed Duty Cycle for Full-Color

Red Scale Value	Green Scale Value	Blue Scale Value	Landed Duty Cycle
0%	0%	0%	0/100
100%	0%	0%	50/50
0%	100%	0%	20/80
0%	0%	100%	30/70
12%	0%	0%	6/94
0%	35%	0%	7/93
0%	0%	60%	18/82
100%	100%	0%	70/30
0%	100%	100%	50/50
100%	0%	100%	80/20
12%	35%	0%	13/87
0%	35%	60%	25/75
12%	0%	60%	24/76
100%	100%	100%	100/0

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8 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

8.1 Application Information

Texas Instruments DLP technology is a micro-electro-mechanical systems (MEMS) technology that modulates light using a digital micromirror device (DMD). DMDs vary in resolution and size and can contain over 8 million micromirrors. Each micromirror of a DMD can represent either one or more pixels on the display and is independently controlled, synchronized with color sequential illumination, to create stunning images on any surface. DLP technology enables a wide variety of display products worldwide, from tiny projection modules embedded in smartphones to high powered digital cinema projectors, and emerging display products such as digital signage and laser TV.

The most recent class of chipsets from Texas Instruments is based on a breakthrough micromirror technology, called TRP. With a smaller pixel pitch of $5.4~\mu m$ and increased tilt angle of 17 degrees, TRP chipsets enable higher resolution in a smaller form factor and enhanced image processing features while maintaining high optical efficiency. DLP chipsets are a great fit for any system that requires high resolution and high brightness displays.

8.2 Typical Application

The DLP660TE DMD is the first full 4K UHD DLP digital micromirror device. When combined with two display controllers (DLPC4422), an FPGA, a power management device (DLPA100), and other electrical, optical and mechanical components the chipset enables bright, affordable, full 4K UHD display solutions. A typical 4K UHD system application using the DLP660TE DMD is shown in Figure 12.

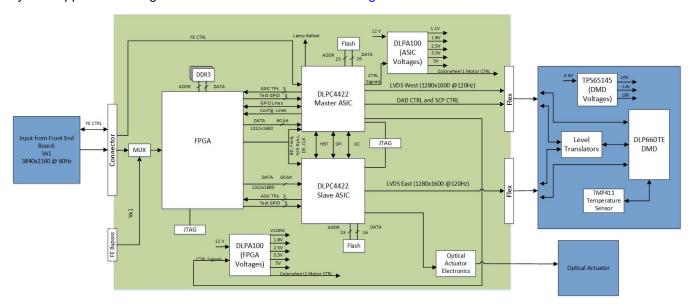


Figure 12. Typical 4K UHD Application Diagram



Typical Application (continued)

8.2.1 Design Requirements

At the high level, DLP660TE DMD systems will include an illumination source, a light engine, electronic components, and software. The designer must first choose an illumination source and design the optical engine taking into consideration the relationship between the optics and the illumination source. The designer must then understand the electronic components of a DLP660TE DMD system, which is made up of a DMD board and formatter board. The DMD board channels image data to and powers the DMD chip. The formatter board supports the rest of the electronic components, which can include an FPGA, the DLPC4422 display controller, power supplies, and drivers for illumination sources, color wheels, fans, and dynamic optical components.

8.2.2 Detailed Design Procedure

For connecting together the DLPC4422 display controller and the DLP660TE DMD, see the reference design schematic. Layout guidelines should be followed to achieve a reliable projector. To complete the DLP system an optical module or light engine is required that contains the DLP660TE DMD, associated illumination sources, optical elements, and necessary mechanical components.

8.2.3 Application Curves

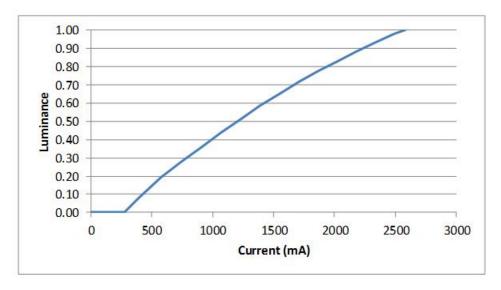


Figure 13. Luminance vs. Current

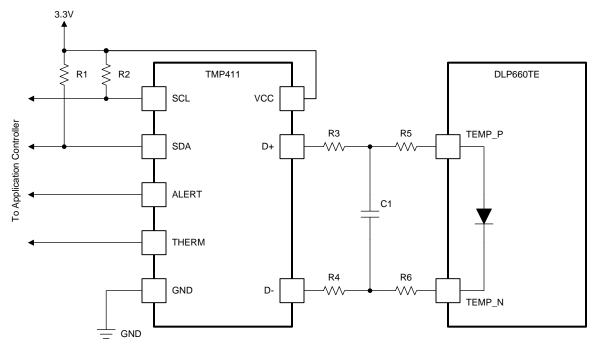
8.3 DMD Die Temperature Sensing

The DMD features a built-in thermal diode that measures the temperature at one corner of the die outside the micromirror array. The thermal diode can be interfaced with the TMP411 temperature sensor as shown in Figure 14. The serial bus from the TMP411 can be connected to the DLPC4422 display controller to enable its temperature sensing features. See the DLPC4422 Programmers' Guide for instructions on installing the DLPC4422 controller support firmware bundle and obtaining the temperature readings.

The software application contains functions to configure the TMP411 to read the DMD temperature sensor diode. This data can be leveraged to incorporate additional functionality in the overall system design such as adjusting illumination, fan speeds, and so forth. All communication between the TMP411 and the DLPC4422 controller will be completed using the I²C interface. The TMP411 connects to the DMD via pins E16 and E17 as outlined in *Pin Configuration and Functions*.



DMD Die Temperature Sensing (continued)



- (1) Details omitted for clarity, see the TI Reference Design for connections to the DLPC4422 controller.
- (2) See the TMP411 datasheet for system board layout recommendation.
- (3) See the TMP411 datasheet and the TI reference design for suggested component values for R1, R2, R3, R4, and C1.
- (4) R5 = 0 Ω . R6 = 0 Ω . Zero ohm resistors should be located close to the DMD package pins.

Figure 14. TMP411 Sample Schematic

TEXAS INSTRUMENTS

9 Power Supply Recommendations

The following power supplies are all required to operate the DMD:

- VSS
- VCC
- VCCI
- VBIAS
- VOFFSET
- VRESET

DMD power-up and power-down sequencing is strictly controlled by the DLP display controller.

CAUTION

For reliable operation of the DMD, the following power supply sequencing requirements must be followed. Failure to adhere to any of the prescribed power-up and power-down requirements may affect device reliability. See Figure 15 DMD Power Supply Sequencing Requirements.

VBIAS, VCC, VCCI, VOFFSET, and VRESET power supplies must be coordinated during power-up and power-down operations. Failure to meet any of the below requirements will result in a significant reduction in the DMD's reliability and lifetime. Common ground VSS must also be connected.

9.1 DMD Power Supply Power-Up Procedure

- During power-up, VCC and VCCI must always start and settle before VOFFSET plus Delay1 specified in Table 8, VBIAS, and VRESET voltages are applied to the DMD.
- During power-up, it is a strict requirement that the voltage delta between VBIAS and VOFFSET must be within the specified limit shown in Recommended Operating Conditions.
- During power-up, there is no requirement for the relative timing of VRESET with respect to VBIAS.
- Power supply slew rates during power-up are flexible, provided that the transient voltage levels follow the requirements specified in *Absolute Maximum Ratings*, in *Recommended Operating Conditions*, and in Figure 15.
- During power-up, LVCMOS input pins must not be driven high until after VCC and VCCI have settled at operating voltages listed in Recommended Operating Conditions.

9.2 DMD Power Supply Power-Down Procedure

- During power-down, VCC and VCCI must be supplied until after VBIAS, VRESET, and VOFFSET are discharged to within the specified limit of ground. See Table 8.
- During power-down, it is a strict requirement that the voltage delta between VBIAS and VOFFSET must be within the specified limit shown in Recommended Operating Conditions.
- During power-down, there is no requirement for the relative timing of VRESET with respect to VBIAS.
- Power supply slew rates during power-down are flexible, provided that the transient voltage levels follow the requirements specified in *Absolute Maximum Ratings*, in *Recommended Operating Conditions*, and in Figure 15.
- During power-down, LVCMOS input pins must be less than specified in Recommended Operating Conditions.

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DMD Power Supply Power-Down Procedure (continued)

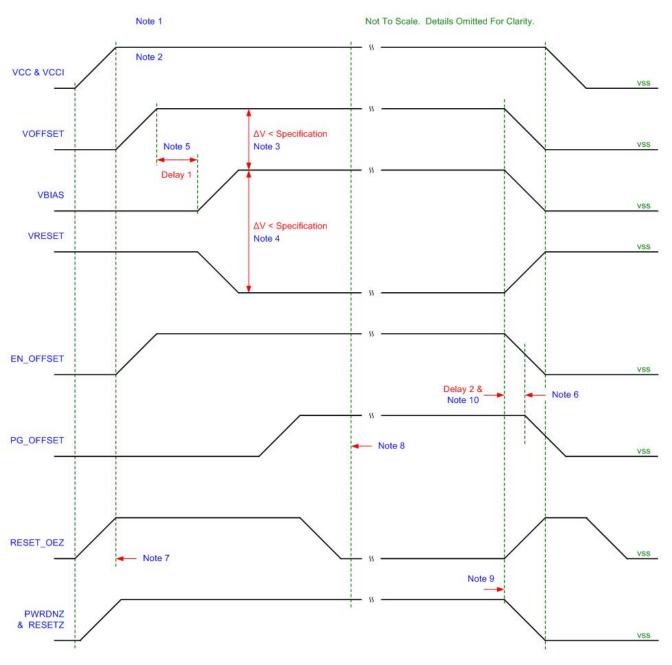


Figure 15. DMD Power Supply Requirements

- 1. See Recommended Operating Conditions, Pin Functions.
- 2. To prevent excess current, the supply voltage delta |VCCI VCC| must be less than specified limit in Recommended Operating Conditions.
- 3. To prevent excess current, the supply voltage delta |VBIAS VOFFSET| must be less than specified in Recommended Operating Conditions.
- 4. To prevent excess current, the supply voltage delta |VBIAS VRESET| must be less than specified limit in *Recommended Operating Conditions*.
- 5. VBIAS should power up after VOFFSET has powered up, per the Delay1 specification in Table 8.
- 6. PG_OFFSET should turn off after EN_OFFSET has turned off, per the Delay2 specification in Table 8.



DMD Power Supply Power-Down Procedure (continued)

- 7. DLP controller software enables the DMD power supplies to turn on after RESET_OEZ is at logic high.
- 8. DLP controller software initiates the global VBIAS command.
- 9. After the DMD micromirror park sequence is complete, the DLP controller software initiates a hardware power-down that activates PWRDNZ and disables VBIAS, VRESET and VOFFSET.
- 10. Under power-loss conditions where emergency DMD micromirror park procedures are being enacted by the DLP controller hardware, EN_OFFSET may turn off after PG_OFFSET has turned off. The OEZ signal should go high prior to PG_OFFSET turning off to indicate the DMD micromirror has completed the emergency park procedures.

Table 8. DMD Power-Supply Requirements

Parameter	Description	Min	NOM	Max	Unit
Delay1	Delay from VOFFSET settled at recommended operating voltage to VBIAS and VRESET power up	1	2		ms
Delay2	PG_OFFSET hold time after EN_OFFSET goes low	100			ns

10 Layout

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10.1 Layout Guidelines

The DLP660TE DMD is part of a chipset that is controlled by the DLPC4422 display controller in conjunction with the DLPA100 power and motor driver. These guidelines are targeted at designing a PCB board with the DLP660TE DMD. The DLP660TE DMD board is a high-speed multi-layer PCB, with primarily high-speed digital logic utilizing dual edge clock rates up to 400MHz for DMD LVDS signals. The remaining traces are comprised of low speed digital LVTTL signals. TI recommends that mini power planes are used for VOFFSET, VRESET, and VBIAS. Solid planes are required for DMD_P3P3V(3.3V), DMD_P1P8V and Ground. The target impedance for the PCB is 50 Ω ±10% with the LVDS traces being 100 Ω ±10% differential. TI recommends using an 8 layer stack-up as described in Table 9.

10.2 Layout Example

10.2.1 Layers

The layer stack-up and copper weight for each layer is shown in Table 9. Small sub-planes are allowed on signal routing layers to connect components to major sub-planes on top/bottom layers if necessary.

LAYER NO.	LAYER NAME	COPPER WT. (oz.)	COMMENTS						
1	Side A - DMD only	1.5	DMD, escapes, low frequency signals, power sub-planes.						
2	Ground	1	Solid ground plane (net GND).						
3	Signal	0.5	50 Ω and 100 Ω differential signals						
4	Ground	1	Solid ground plane (net GND)						
5	DMD_P3P3V	1	+3.3-V power plane (net DMD_P3P3V)						
6	Signal	0.5	50 Ω and 100 Ω differential signals						
7	Ground	1	Solid ground plane (net GND).						
8	Side B - All other Components	1.5	Discrete components, low frequency signals, power sub-planes						

Table 9. Layer Stack-Up

10.2.2 Impedance Requirements

TI recommends that the board has matched impedance of 50 Ω ±10% for all signals. The exceptions are listed in Table 10.

Signal Type Signal Name Impedance (ohms) D_AP(0:15), D_AN(0:15) 100 ±10% differential across A channel LVDS differential pairs DCLKA_P, DCLKA_N each pair SCTRL_AP, SCTRL_AN D_BP(0:15), D_BN(0:15) 100 ±10% differential across B channel LVDS differential pairs DCLKB_P, DCLKB_N each pair SCTRL_BP, SCTRL_BN D_CP(0:15), D_CN(0:15) 100 ±10% differential across C channel LVDS differential pairs DCLKC_P, DCLKC_N each pair SCTRL_CP, SCTRL_CN D_DP(0:15), D_DN(0:15) 100 ±10% differential across D channel LVDS differential pairs DCLKD_P, DCLKD_N each pair SCTRL_DP, SCTRL_DN

Table 10. Special Impedance Requirements

TEXAS INSTRUMENTS

10.2.3 Trace Width, Spacing

Unless otherwise specified, TI recommends that all signals follow the 0.005"/0.005" design rule. Minimum trace clearance from the ground ring around the PWB has a 0.1" minimum. An analysis of impedance and stack-up requirements determine the actual trace widths and clearances.

10.2.3.1 Voltage Signals

Table 11. Special Trace Widths, Spacing Requirements

SIGNAL NAME	MINIMUM TRACE WIDTH TO PINS (MIL)	LAYOUT REQUIREMENT				
GND	15	Maximize trace width to connecting pin				
DMD_P3P3V	15	Maximize trace width to connecting pin				
DMD_P1P8V	15	Maximize trace width to connecting pin				
VOFFSET	15	Create mini plane from U2 to U3				
VRESET	15	Create mini plane from U2 to U3				
VBIAS	15	Create mini plane from U2 to U3				
All U3 control connections	10	Use 10 mil etch to connect all signals/voltages to DMD pads				

11 Device and Documentation Support

11.1 Device Support

11.1.1 Device Nomenclature

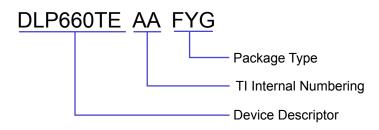


Figure 16. Part Number Description

11.1.2 Device Markings

The device marking will include both human-readable information and a 2-dimensional matrix code. The human-readable information is described in Figure 17. The 2-dimensional matrix code is an alpha-numeric character string that contains the DMD part number, Part 1 of Serial Number, and Part 2 of Serial Number. The first character of the DMD Serial Number (part 1) is the manufacturing year. The second character of the DMD Serial Number (part 1) is the manufacturing month. The last character of the DMD Serial Number (part 2) is the bias voltage bin letter.

Example: *2715-7032 GHXXXXX LLLLLLM

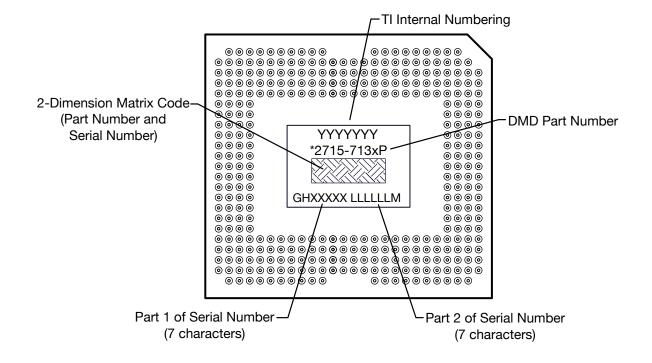


Figure 17. DMD Marking Locations



11.2 Documentation Support

11.2.1 Related Documentation

The following documents contain additional information related to the chipset components used with the DLP660TE:

- DLPC4422 Display Controller
- DLPA100 Power and Motor Driver Data Sheet

11.3 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. In the upper right corner, click on *Alert me* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

11.4 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

TI E2E™ Online Community TI's Engineer-to-Engineer (E2E) Community. Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

Design Support *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

11.5 Trademarks

E2E is a trademark of Texas Instruments.

DLP is a registered trademark of Texas Instruments.

11.6 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

11.7 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.

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12 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.



PACKAGE OPTION ADDENDUM

5-Jun-2019

PACKAGING INFORMATION

Orderable Device	Status	Package Type	_	Pins	_	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)	(6)	(3)		(4/5)	
DLP660TEAAFYG	ACTIVE	CPGA	FYG	350	1	RoHS & non-Green	Call TI	Call TI			Samples
DLP660TEFYG	OBSOLETE	CPGA	FYG	350		TBD	Call TI	Call TI			

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

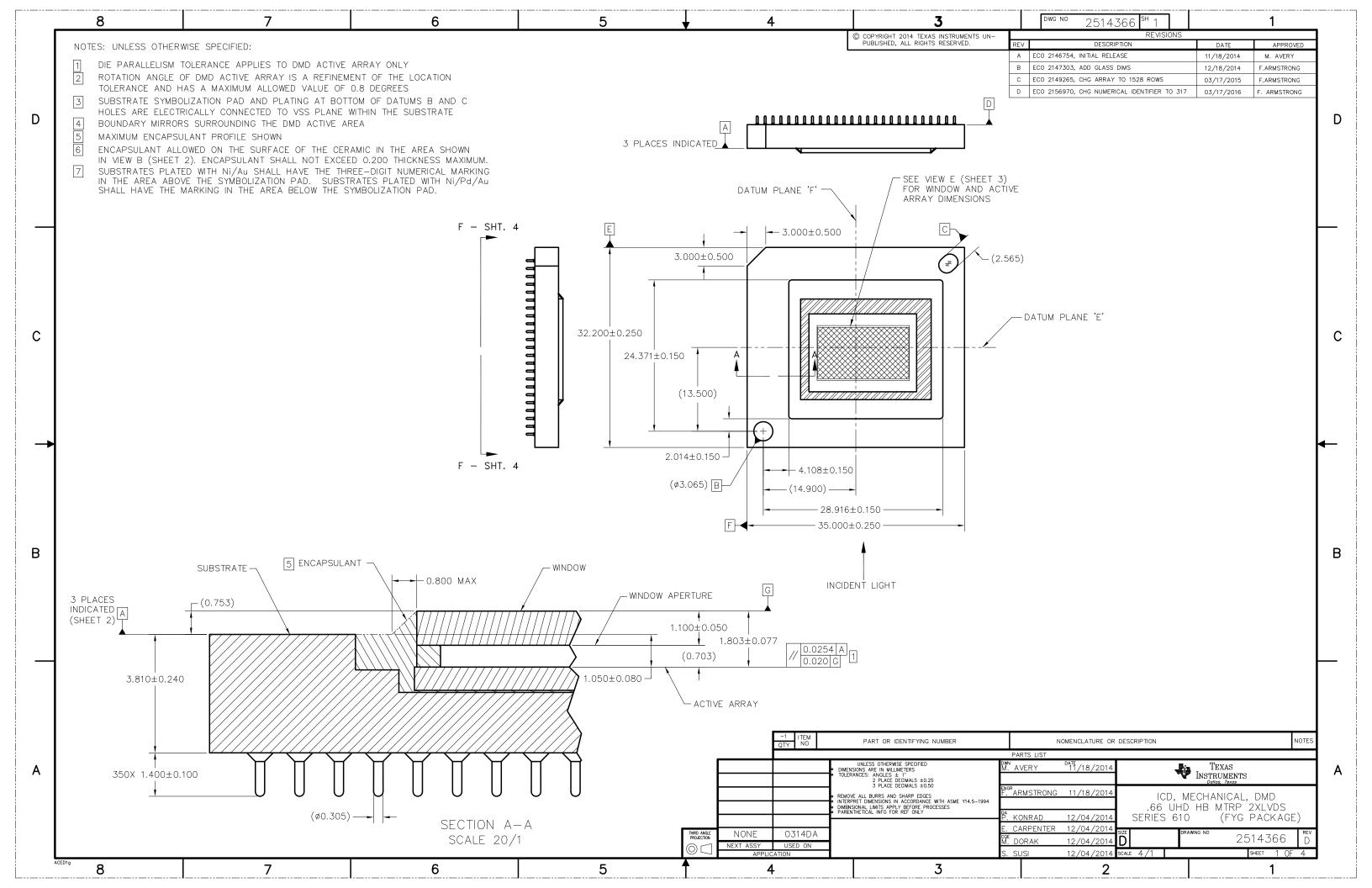
RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

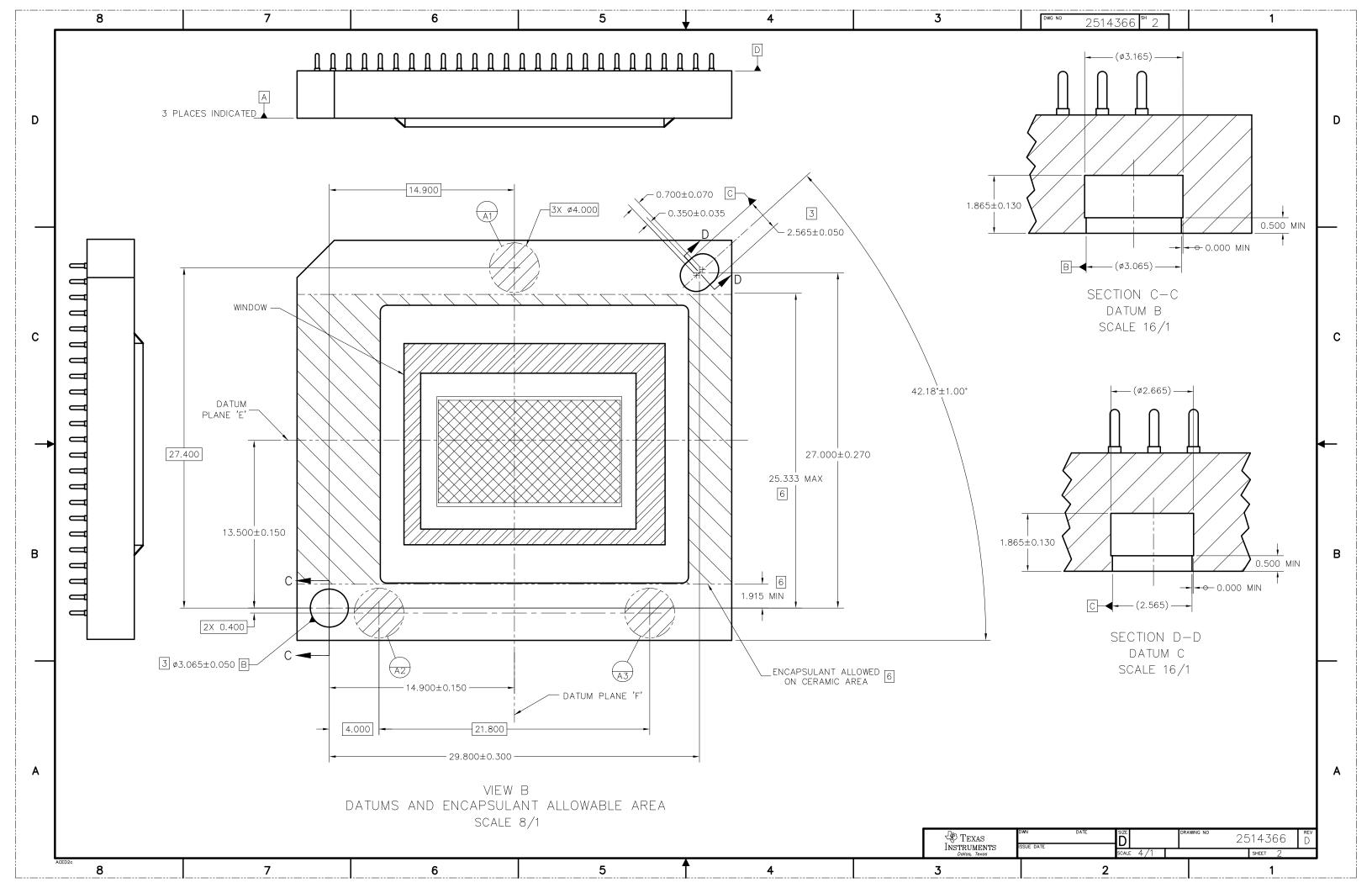
Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

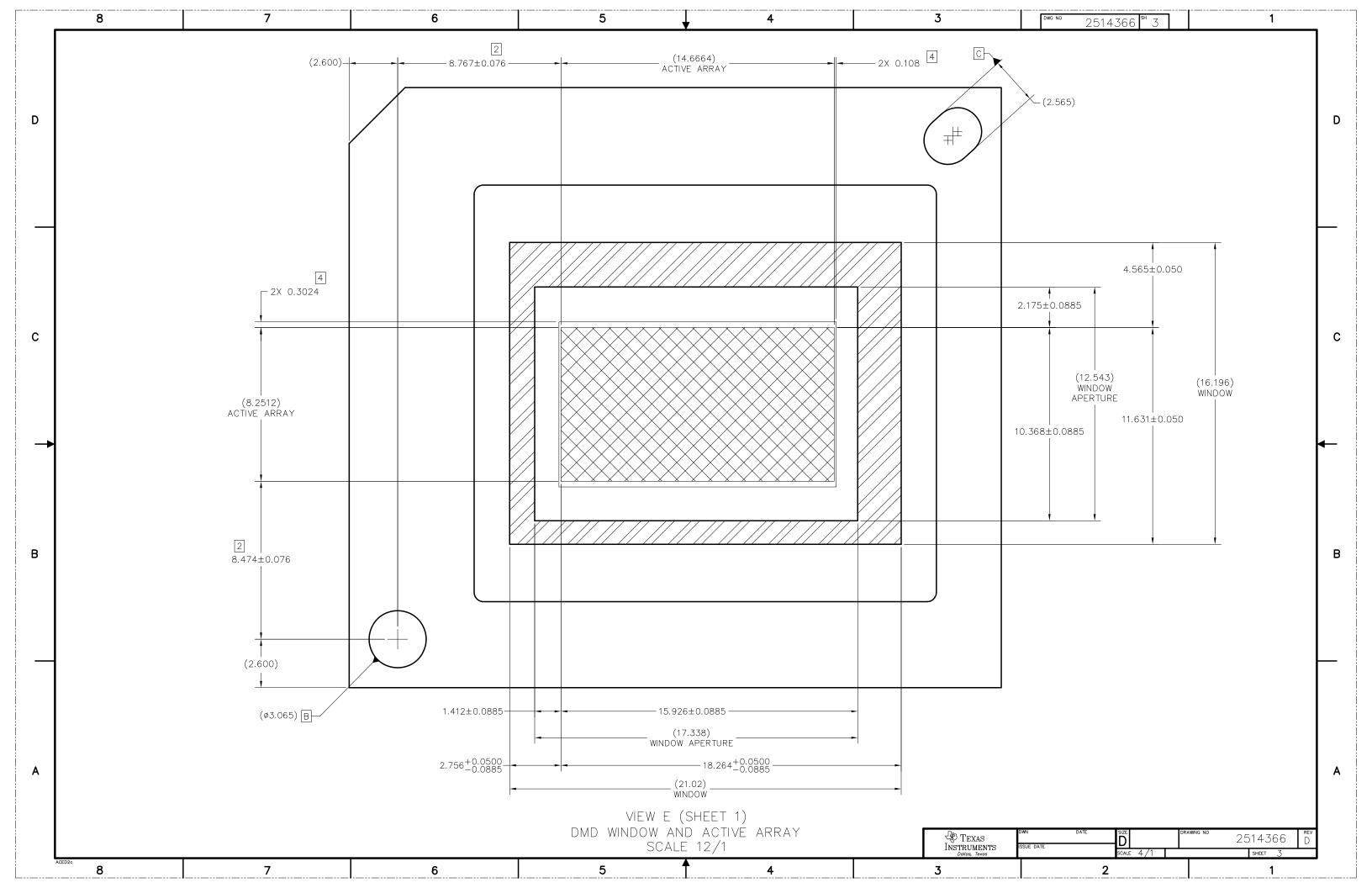
- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead/Ball Finish Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

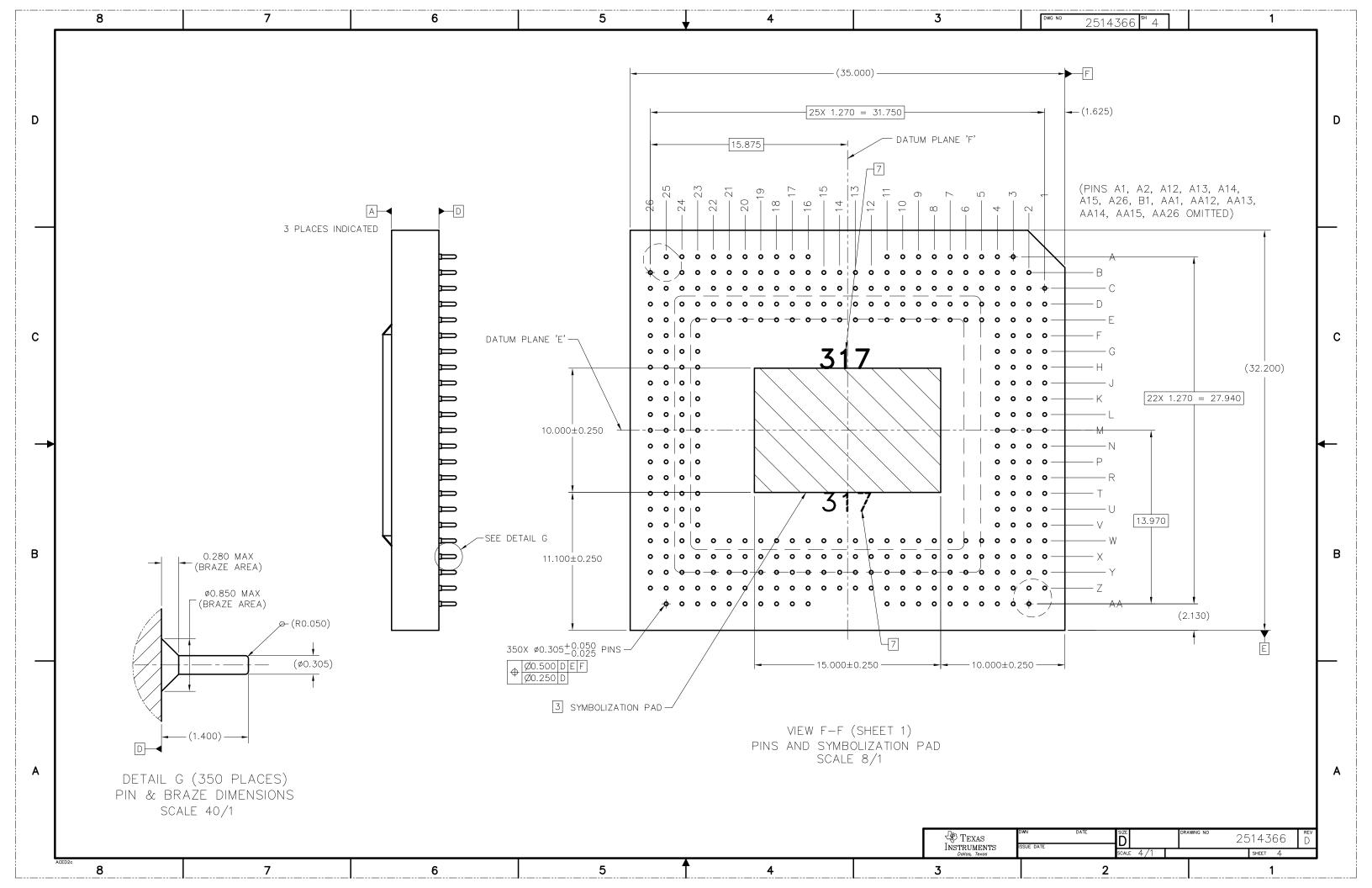
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